

# HAT2208R

Silicon N Channel Power MOS FET Power Switching

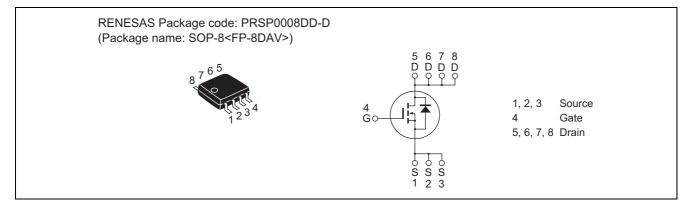
> REJ03G1595-0200 Rev.2.00 Oct 15, 2007

# Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)} = 19.0 \text{ m}\Omega \text{ typ.}$  (at  $V_{GS} = 10 \text{ V}$ )

# Outline



# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	30	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	9	A
Drain peak current	I <sub>D(pulse)</sub> Note1	72	A
Body-drain diode reverse drain current	I <sub>DR</sub>	9	A
Avalanche current	I <sub>AP</sub> Note 2	9	A
Avalanche energy	E <sub>AR</sub> Note 2	8.1	mJ
Channel dissipation	Pch Note3	2.0	W
Channel to ambient thermal impedance	θch-a <sup>Note3</sup>	62.5	°C/W
Channel temperature	Tch	150	٥C
Storage temperature	Tstg	-55 to +150	۵°

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

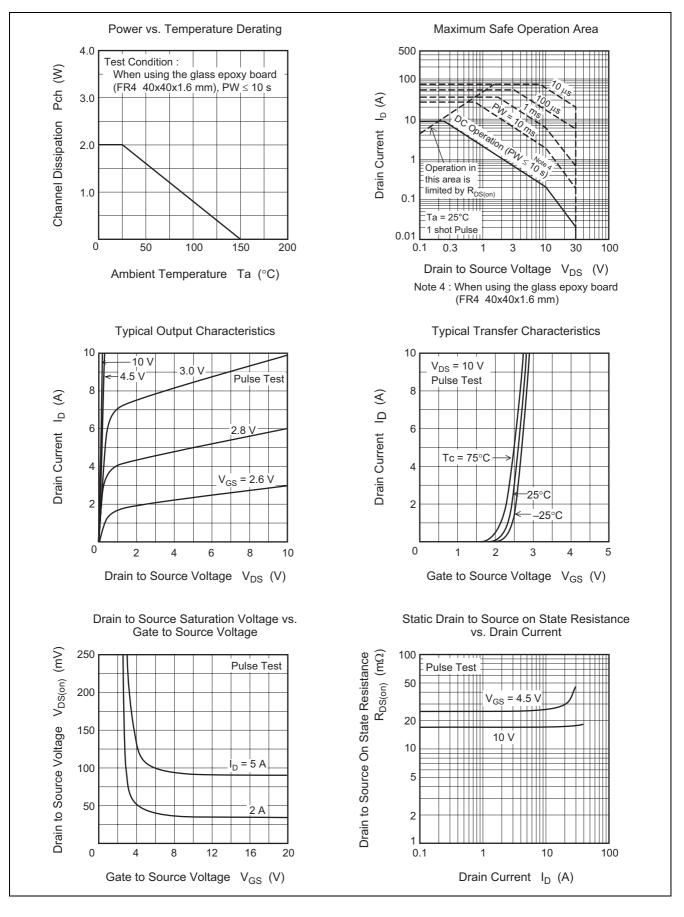
- 2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW  $\leq$  10s

# **Electrical Characteristics**

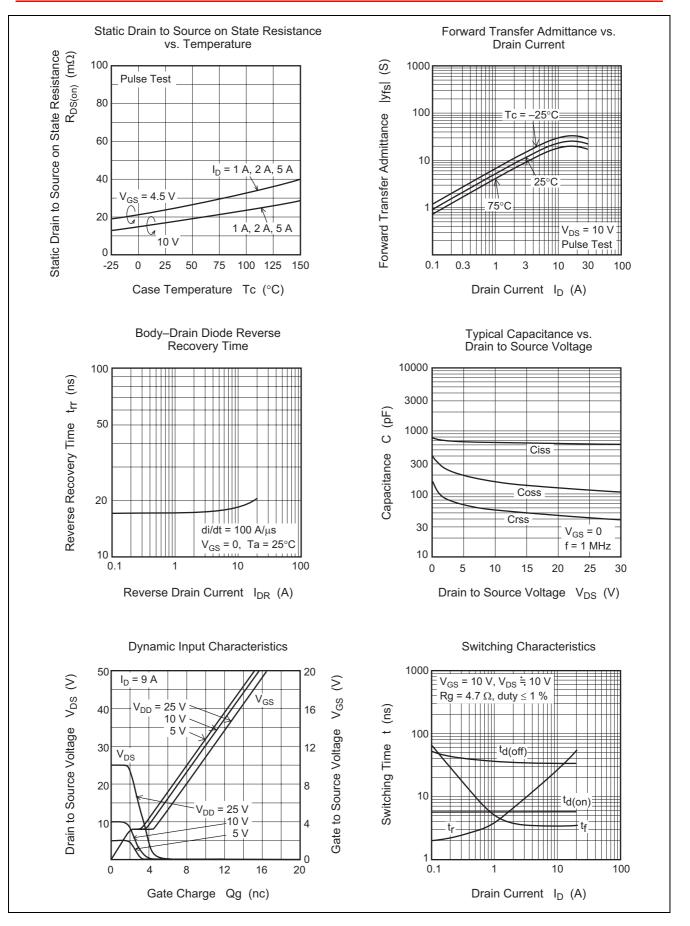
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	30	_	—	V	$I_{D} = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>		_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>		—	1	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	1.0	—	2.5	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>		19	24	mΩ	$I_D = 4.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance	R <sub>DS(on)</sub>		24	35	mΩ	$I_D = 4.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{Note4}$
Forward transfer admittance	y <sub>fs</sub>	9.5	16	_	S	$I_D = 4.5 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	630	—	pF	V <sub>DS</sub> = 10 V
Output capacitance	Coss	_	160	—	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	56	—	pF	
Gate Resistance	Rg		1.1	—	Ω	
Total gate charge	Qg		4.4	—	nC	V <sub>DD</sub> = 10 V V <sub>GS</sub> = 4.5 V I <sub>D</sub> = 9 A
Gate to source charge	Qgs		2.2	—	nC	
Gate to drain charge	Qgd		1.4	—	nC	
Turn-on delay time	t <sub>d(on)</sub>		5.8	—	ns	
Rise time	tr		15	—	ns	
Turn-off delay time	t <sub>d(off)</sub>		34	—	ns	
Fall time	t <sub>f</sub>		3.5	—	ns	
Body-drain diode forward voltage	V <sub>DF</sub>	_	0.84	1.10	V	$IF = 9 A, V_{GS} = 0^{Note4}$
Body–drain diode reverse recovery	t <sub>rr</sub>	_	18		ns	IF = 9 A, V <sub>GS</sub> = 0
time						di <sub>F</sub> / dt = 100 A/ μs

Notes: 4. Pulse test

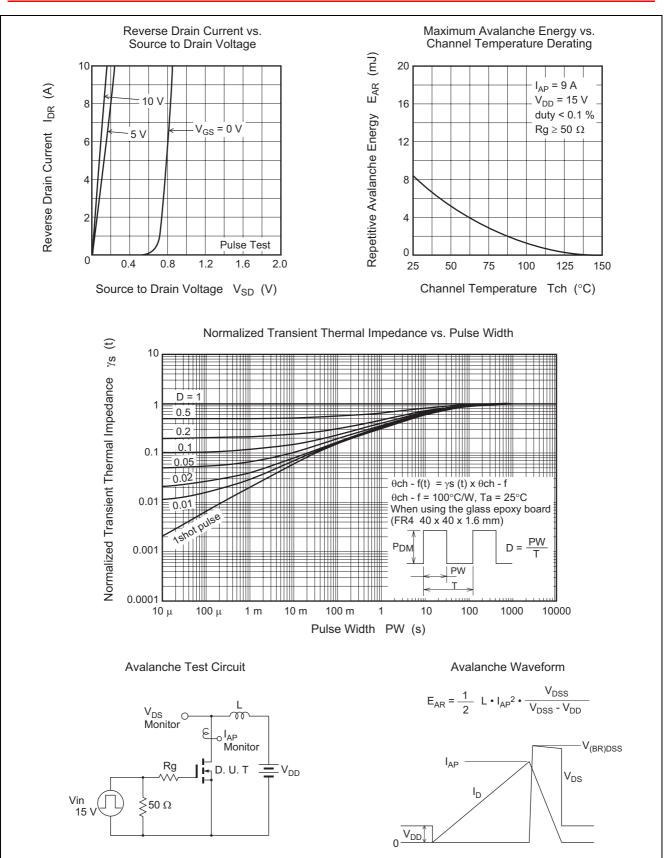
# **Main Characteristics**



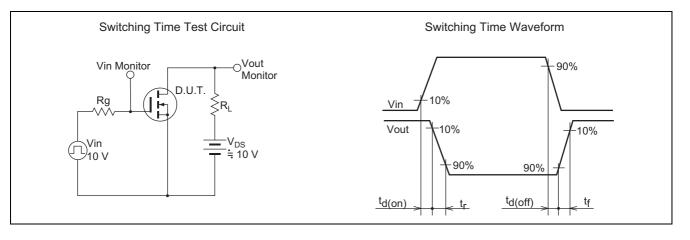
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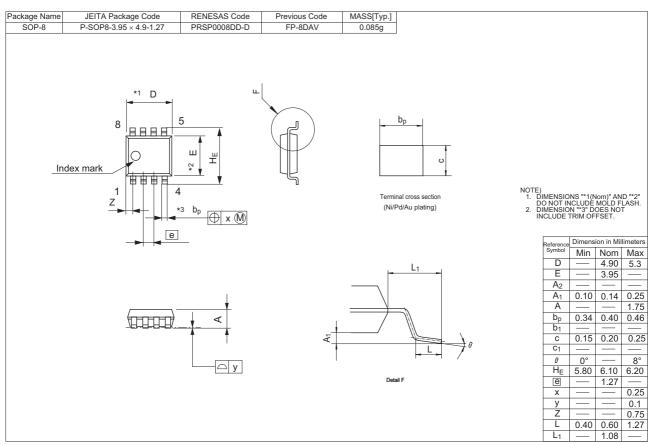
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# **Package Dimensions**



# **Ordering Information**

Part Name	Quantity	Shipping Container
HAT2208R-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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